

Features

- Trench/Fieldstop IGBT
- LOW V_{CESAT}
- Al₂O₃ Substrate with Low Thermal Resistance
- Standard Housing
- Copper Base Plate
- Solder Contact Technology
- Integrated NTC temperature sensor



Typical Applications

- Motor Drives
- Servo Drives
- Auxiliary Inverters

IGBT, Inverter

Maximum Rated Values							
Symbol	Item	Conditions	Rating			Unit	
IGBT							
V_{CES}	Collector-emitter voltage	$T_{vj}=25^{\circ}C$	1200			V	
V_{GES}	Gate-emitter voltage	-	± 20			V	
I_C	Collector current,DC	$T_C=100^{\circ}C, T_{vj}=175^{\circ}C$	75			A	
I_{CRM}	Repetitive peak collector current	$t_p=1ms$	150			A	
P_{tot}	Total power dissipation	$T_C=25^{\circ}C, T_{vj}=175^{\circ}C$	375			W	
Characteristics Values							
Symbol	Item	Conditions	Values			Unit	
IGBT			Min.	Typ.	Max.		
I_{CES}	Collector-emitter cut-off current	$V_{CE}=1200V, V_{GE}=0V, T_{vj}=25^{\circ}C$	-	-	1	mA	
I_{GES}	Gate leakage current	$V_{CE}=0V, V_{GE}=20V, T_{vj}=25^{\circ}C$	-	-	100	nA	
$V_{GE(th)}$	Gate-emitter threshold voltage	$I_C=2.4mA, V_{CE}=V_{GE}, T_{vj}=25^{\circ}C$	5.2	5.95	6.6	V	
V_{CESat}	Collector-emitter saturation voltage	$I_C=75A$ $V_{GE}=15V$	$T_{vj}=25^{\circ}C$	-	1.83		-
			$T_{vj}=125^{\circ}C$	-	-		-
			$T_{vj}=150^{\circ}C$	-	-	-	
C_{ies}	Input capacitance	$V_{CE}=25V, V_{GE}=0V$ $f=1MHz, T_{vj}=25^{\circ}C$	-	5.3	-	nF	
C_{oes}	Output capacitance		-	0.35	-		
C_{res}	Reverse transfer capacitance		-	0.18	-		
Q_G	Gate charge	$V_{CC}=600V, I_C=75A$ $V_{GE}=-15...+15V, T_{vj}=25^{\circ}C$	-	0.477	-	μC	
R_g	Internal gate resistance	$T_{vj}=25^{\circ}C$	-	2.4	-	Ω	

$t_{d(on)}$	Turn-on delay time	$V_{CC}=600V$ $I_C=75A$ $V_{GE}=\pm 15V$ $R_{G(on)}=20\Omega$ $R_{G(off)}=20\Omega$	$T_{vj}=25^\circ C$	-	103.2	-	ns
			$T_{vj}=125^\circ C$	-	-	-	
			$T_{vj}=150^\circ C$	-	-	-	
t_r	Rise time		$T_{vj}=25^\circ C$	-	60.8	-	
			$T_{vj}=125^\circ C$	-	-	-	
			$T_{vj}=150^\circ C$	-	-	-	
$t_{d(off)}$	Turn-off delay time		$T_{vj}=25^\circ C$	-	471.7	-	
			$T_{vj}=125^\circ C$	-	-	-	
			$T_{vj}=150^\circ C$	-	-	-	
t_f	Fall time		$T_{vj}=25^\circ C$	-	248.2	-	
			$T_{vj}=125^\circ C$	-	-	-	
			$T_{vj}=150^\circ C$	-	-	-	
E_{on}	Turn-on energy (per pulse)	$T_{vj}=25^\circ C$	-	13.7	-	mJ	
		$T_{vj}=125^\circ C$	-	-	-		
		$T_{vj}=150^\circ C$	-	-	-		
E_{off}	Turn-off energy (per pulse)	$T_{vj}=25^\circ C$	-	4.8	-		
		$T_{vj}=125^\circ C$	-	-	-		
		$T_{vj}=150^\circ C$	-	-	-		
SC data	Short-circuit current	$V_{CC}=600V, V_{GE}\leq 15V, T_{vj}=125^\circ C$ $V_{CES}\leq 1200V, t_p\leq 10\mu s$	-	386	-	A	
R_{thJC}	Thermal resistance, junction to case	Per IGBT	-	-	0.4	K/W	
R_{thCH}	Thermal resistance, case to heatsink	Per IGBT $\lambda_{grease}=1W/(m\cdot K)$	-	0.13	-	K/W	
T_{vjop}	Temperature under switching conditions		-40		150	$^\circ C$	

**Diode, Inverter
Maximum Rated Values**

Symbol	Item	Conditions	Rating	Unit
V_{RRM}	Repetitive peak reverse voltage	$T_{vj}=25^\circ C$	1200	V
I_F	Forward current, DC		75	A
I_{FRM}	Repetitive peak forward current	$t_p=1ms$	150	A
I^2t	I^2t -value	$V_R=0V, t_p=10ms, T_{vj}=125^\circ C$	960	A^2s

Characteristic Values

			Min.	Typ.	Max.		
V_F	Continuous forward voltage	$I_F=75A$ $V_{GE}=0V$	$T_{vj}=25^\circ C$	-	1.86	-	V
			$T_{vj}=125^\circ C$	-	-	-	
			$T_{vj}=150^\circ C$	-	-	-	
I_{RM}	Peak reverse recovery current	$V_R=600V$ $I_F=75A$ $V_{GE}=-15V$	$T_{vj}=25^\circ C$	-	52.8	-	A
			$T_{vj}=125^\circ C$	-	-	-	
			$T_{vj}=150^\circ C$	-	-	-	
t_{rr}	Reverse recovery time		$T_{vj}=25^\circ C$	-	76.6	-	ns
			$T_{vj}=125^\circ C$	-	-	-	
			$T_{vj}=150^\circ C$	-	-	-	
Q_r	Recovered charge	$T_{vj}=25^\circ C$	-	2.26	-	μC	
		$T_{vj}=125^\circ C$	-	-	-		
		$T_{vj}=150^\circ C$	-	-	-		

E _{rec}	Reverse recovery energy		T _{vj} =25°C	-	0.27	-	mJ
			T _{vj} =125°C	-	-	-	
			T _{vj} =150°C	-	-	-	
R _{thJC}	Thermal resistance, junction to case	Per diode		-	-	0.68	K/W
R _{thCH}	Thermal resistance, case to heatsink	Per diode, λ _{grease} = 1 W/(mK)			0.13		K/W
T _{vjop}	Temperature under switching conditions			-40		150	°C

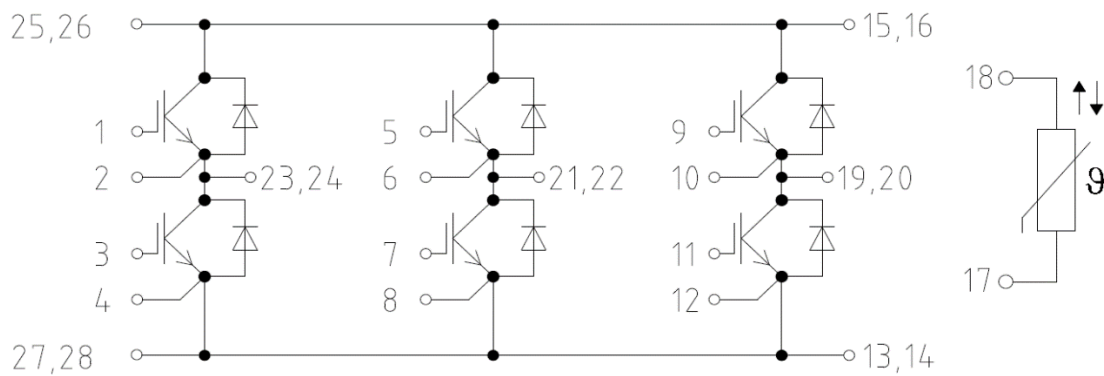
NTC Thermistor Characteristics

Symbol	Item	Conditions	Values			Unit
			Min.	Typ.	Max.	
R ₂₅	Rated resistance	T _C =25°C	-	5	-	kΩ
ΔR/R	Deviation of resistance	T _C =100°C, R ₁₀₀ =493Ω	-5	-	5	%
P ₂₅	Power dissipation	T _C =25°C	-	-	20	mW
B _{25/50}	B-constant	R ₂ =R ₂₅ exp[B _{25/50} (1/T ₂ -1/(298.15K))]	-	3375	-	K
B _{25/80}	B-constant	R ₂ =R ₂₅ exp[B _{25/80} (1/T ₂ -1/(298.15K))]	-	3411	-	
B _{25/100}	B-constant	R ₂ =R ₂₅ exp[B _{25/100} (1/T ₂ -1/(298.15K))]	-	3433	-	

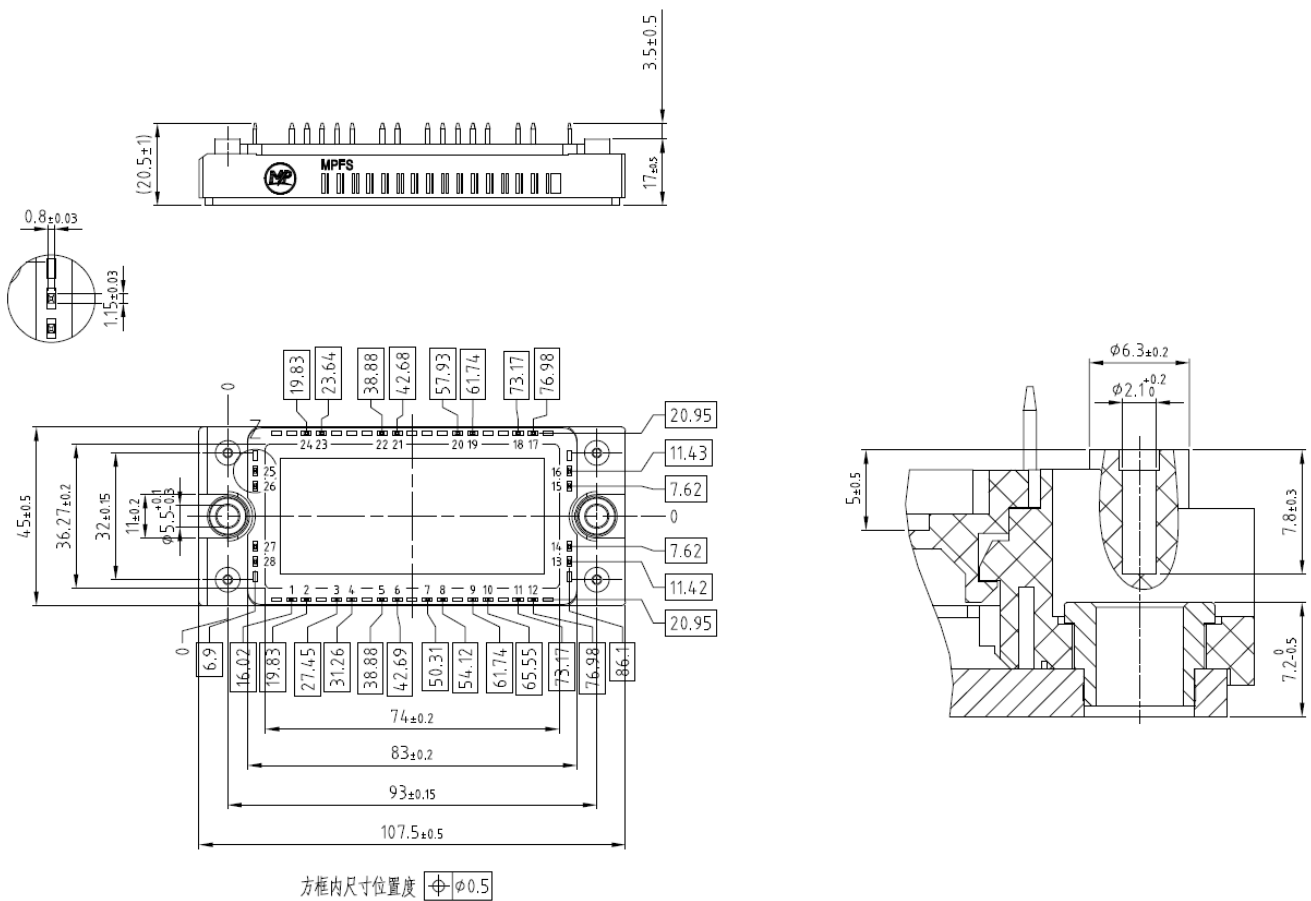
Module

Symbol	Item	Conditions	Rating			Unit
V _{ISOL}	Isolation voltage	Terminals to baseplate, RMS, f=50Hz, t=1min	2500			V
T _{vj max}	Maximum junction temperature	-	175			°C
T _{vj op}	Operating junction temperature	Continuous operation (under switching)	-40~150			°C
T _{stg}	Storage temperature	-	-40~125			°C
Symbol	Item	Conditions	Values			Unit
			Min.	Typ.	Max.	
Ms	Mounting torque	Mounting to heat sink, M5 screw	3	-	6	Nm
ds	Creepage distance	Terminal to terminal	-	-	-	mm
		Terminal to base plate	-	10	-	
da	Clearance	Terminal to terminal	-	-	-	mm
		Terminal to base plate	-	7.5	-	
m	Weight	-	-	175	-	g

Circuit Diagram



Package Outlines



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